DME20C01

Silicon PNP epitaxial planar type (Tr1) Silicon NPN epitaxial planar type (Tr2)

For general amplification

Features

- \bullet High forward current transfer ratio h_{FE} with excellent linearity
- \bullet Low collector-emitter saturation voltage $V_{CE(\text{sat})}$
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)

Marking Symbol: A4

Basic Part Number

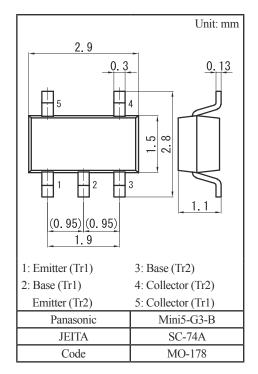
DSA2001 + DSC2001 (Base-emitterr connection)

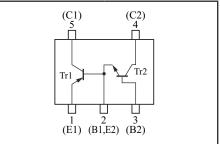
Packaging

DME20C010R Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

Absolute Maximum Ratings $T_a = 25^{\circ}C$

| | Parameter | Symbol | Rating | Unit | |
|---------|---------------------------------------|------------------|-------------|------|--|
| Tr1 | Collector-base voltage (Emitter open) | V _{CBO} | -60 | V | |
| | Collector-emitter voltage (Base open) | V _{CEO} | -50 | V | |
| | Emitter-base voltage (Collector open) | V _{EBO} | -7 | V | |
| | Collector current | I _C | -100 | mA | |
| | Peak collector current | I _{CP} | -200 | mA | |
| Tr2 | Collector-base voltage (Emitter open) | V _{CBO} | 60 | V | |
| | Collector-emitter voltage (Base open) | V _{CEO} | 50 | V | |
| | Emitter-base voltage (Collector open) | V _{EBO} | 7 | V | |
| | Collector current | I _C | 100 | mA | |
| | Peak collector current | I _{CP} | 200 | mA | |
| Overall | Total power dissipation | P _T | 300 | mW | |
| | Junction temperature | Tj | 150 | °C | |
| | Operating ambient temperature | T _{opr} | -40 to +85 | °C | |
| | Storage temperature | T _{stg} | -55 to +150 | °C | |





Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

• Tr1

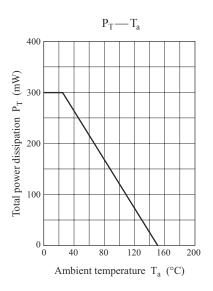
| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|---|----------------------|---|-----|-------|-------|------|
| Collector-base voltage (Emitter open) | V _{CBO} | $I_{\rm C} = -10 \ \mu {\rm A}, I_{\rm E} = 0$ | -60 | | | V |
| Collector-emitter voltage (Base open) | V _{CEO} | $I_{\rm C} = -2 {\rm mA}, I_{\rm B} = 0$ | -50 | | | V |
| Emitter-base voltage (Collector open) | V _{EBO} | $I_{\rm E} = -10 \ \mu A, I_{\rm C} = 0$ | -7 | | | V |
| Collector-base cutoff current (Emitter open) | I _{CBO} | $V_{\rm CB} = -20$ V, $I_{\rm E} = 0$ | | | - 0.1 | μΑ |
| Collector-emitter cutoff current (Base open) | I _{CEO} | $V_{\rm CE} = -10 \text{ V}, I_{\rm B} = 0$ | | | -100 | μΑ |
| Forward current transfer ratio | h _{FE} | $V_{\rm CE} = -10$ V, $I_{\rm C} = -2$ mA | 210 | | 460 | |
| Collector-emitter saturation voltage | V _{CE(sat)} | $I_{\rm C} = -100 \text{ mA}, I_{\rm B} = -10 \text{ mA}$ | | - 0.2 | -0.5 | V |
| Transition frequency | f_{T} | $V_{\rm CE} = -10$ V, $I_{\rm C} = -2$ mA | | 150 | | MHz |
| Collector output capacitance (Common base, input open circuited) | C _{ob} | $V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ | | 2 | | pF |

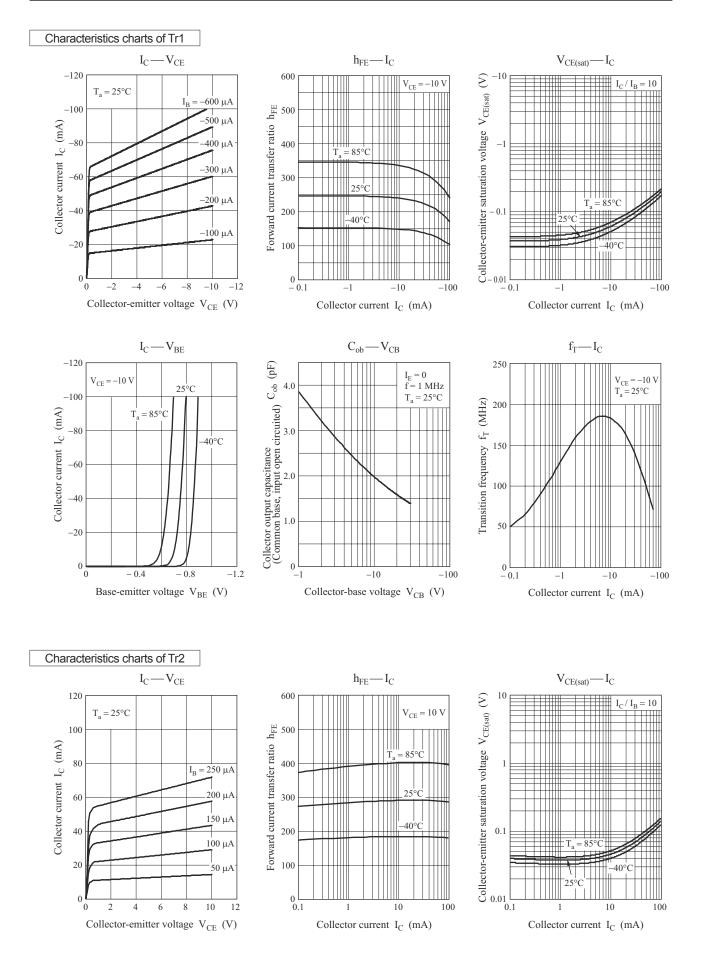
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

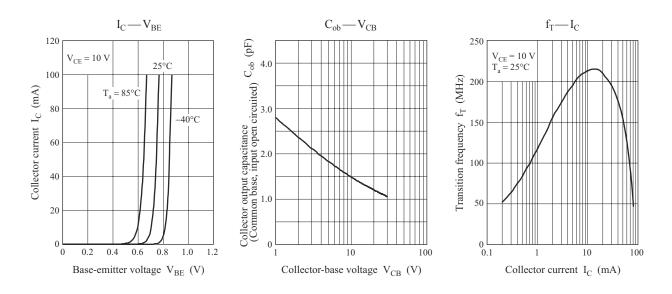
| • Tr2 | | | | | | |
|---|----------------------|---|-----|------|-----|------|
| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
| Collector-base voltage (Emitter open) | V _{CBO} | $I_{\rm C} = 10 \ \mu A, I_{\rm E} = 0$ | 60 | | | V |
| Collector-emitter voltage (Base open) | V _{CEO} | $I_{\rm C} = 2 {\rm mA}, I_{\rm B} = 0$ | 50 | | | V |
| Emitter-base voltage (Collector open) | V _{EBO} | $I_{\rm E} = 10 \ \mu A, I_{\rm C} = 0$ | 7 | | | V |
| Collector-base cutoff current (Emitter open) | I _{CBO} | $V_{CB} = 20 \text{ V}, I_E = 0$ | | | 0.1 | μΑ |
| Collector-emitter cutoff current (Base open) | I _{CEO} | $V_{CE} = 10 \text{ V}, I_{B} = 0$ | | | 100 | μΑ |
| Forward current transfer ratio | h _{FE} | $V_{CE} = 10 \text{ V}, I_C = 2 \text{ mA}$ | 210 | | 460 | |
| Collector-emitter saturation voltage | V _{CE(sat)} | $I_{\rm C} = 100 \text{ mA}, I_{\rm B} = 10 \text{ mA}$ | | 0.13 | 0.3 | V |
| Transition frequency | f_{T} | $V_{CE} = 10 \text{ V}, I_C = 2 \text{ mA}$ | | 150 | | MHz |
| Collector output capacitance (Common base, input open circuited) | C _{ob} | $V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ | | 1.5 | | pF |

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

Common characteristics chart

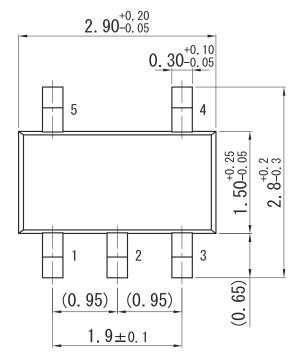


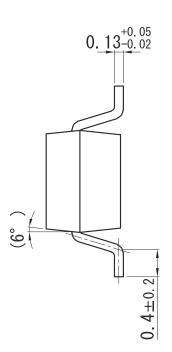


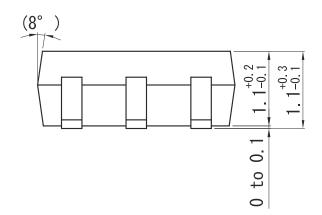


Unit: mm

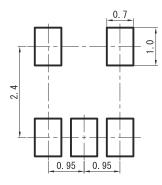
Mini5-G3-B







Land Pattern (Reference) (Unit: mm)



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